



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-220F Plastic-Encapsulate Transistors

3DA5371 TRANSISTOR (NPN)

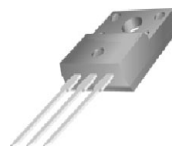
FEATURES

- Breakdown Voltage High
- Reverse Cut-off Current Small
- Saturation Voltage Low
- Power dissipation

$P_{CM} : 1.5W$ ($T_{amb}=25^{\circ}C$)

$25 W$ ($T_{case}=25^{\circ}C$)

TO-220F



1. BASE
2. COLLECTOR
3. EMITTE

MAXIMUM RATINGS ($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	180	V
V_{CEO}	Collector-Emitter Voltage	160	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	1.5	A
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55-150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	180			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	160			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=180V, I_E=0$			10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6V, I_C=0$			10	μA
DC current gain	$h_{FE} *$	$V_{CE}=5V, I_C=200mA$	60		240	
Collector-emitter saturation voltage	$V_{CE(sat)} *$	$I_C=500mA, I_B=50mA$			1	V
Transition frequency	f_T	$V_{CE}=10V, I_C=50mA$	50			MHz

*Pulse test: $t_p \leq 300\mu S$, $\delta \leq 0.02$.

CLASSIFICATION OF h_{FE}

Rank	O	R
Range	60-140	100-240

Typical Characteristics

3DA5371

